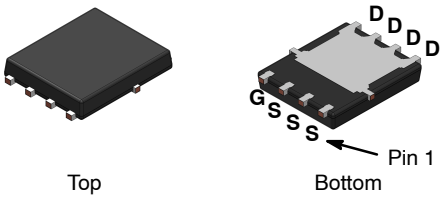
MOSFET – N-Channel, POWERTRENCH®

100 V, 60 A, 8 mΩ

FDMS86101, FDMS86101-NC, FDMS86101-SN00155, FDMS86101-SN00155-NC, FDMS86101-SN00235, FDMS86101-SN00235-NC, FDMS86101-TE, FDMS86101-TE-NC



PQFN8 5x6, 1.27P
(Power 56)
CASE 483AE

General Description

This N-Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

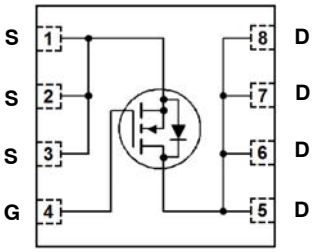
Features

- Max $R_{DS(on)}$ = 8 mΩ at V_{GS} = 10 V, I_D = 13 A
- Max $R_{DS(on)}$ = 13.5 mΩ at V_{GS} = 6 V, I_D = 9.5 A
- Advanced Package and Silicon Combination for Low $R_{DS(on)}$ and High Efficiency
- MSL1 Robust Package Design
- 100% UIL Tested
- 100% Rg Tested
- These Devices are Pb-Free and are RoHS Compliant

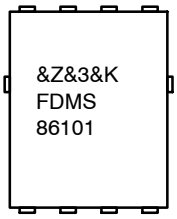
Applications

- DC-DC Conversion

PIN CONNECTIONS



MARKING DIAGRAM



&Z	= Assembly Plant Code
&3	= Data Code (Year & Week)
&K	= Lot Code
FDMS86101	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

MAXIMUM RATINGS (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current: Continuous, T_C = 25 °C Continuous, T_A = 25 °C (Note 1a) Pulsed	 60 12.4 200	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	173	mJ
P_D	Power Dissipation: T_C = 25 °C T_A = 25 °C (Note 1a)	 104 2.5	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		66		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			800	nA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = ±20 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	2.9	4.0	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		−9		mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 13 A		6.3	8	mΩ
		V_{GS} = 6 V, I_D = 9.5 A		8.4	13.5	
		V_{GS} = 10 V, I_D = 13 A, T_J = 125 °C		10.9	14	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 13 A		45		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		2255	3000	pF
C_{oss}	Output Capacitance			460	610	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF
R_g	Gate Resistance		0.1	1.0	3.0	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 13 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		15	27	ns
t_r	Rise Time			11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			27	44	ns
t_f	Fall Time			7	13	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 50 V, I_D = 13 A		39	55	nC
		V_{GS} = 0 V to 5 V, V_{DD} = 50 V, I_D = 13 A		22	31	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 40 V, I_D = 68 A		9.5		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 40 V, I_D = 68 A		10.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.1 A (Note 2)		0.7	1.2	V
		V_{GS} = 0 V, I_S = 13 A (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	I_F = 13 A, di/dt = 100 A/μs		56	90	ns
Q_{rr}	Reverse Recovery Charge			61	98	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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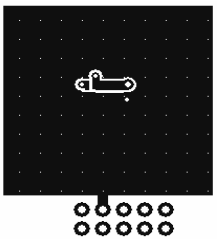
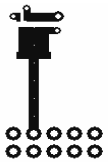
NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 173 mJ is based on starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 34 A, V_{DD} = 75 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 49 A.

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TYPICAL CHARACTERISTICS

(T_J = 25 °C unless otherwise noted)

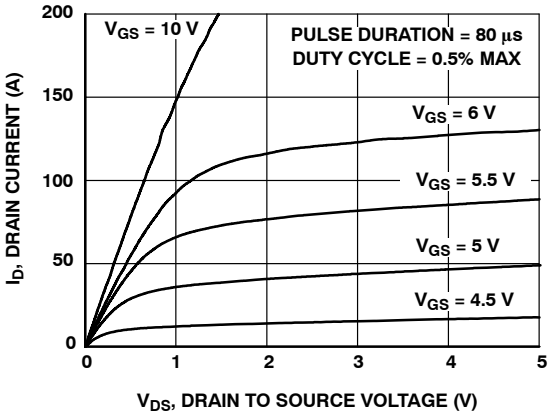

Figure 1. On Region Characteristics

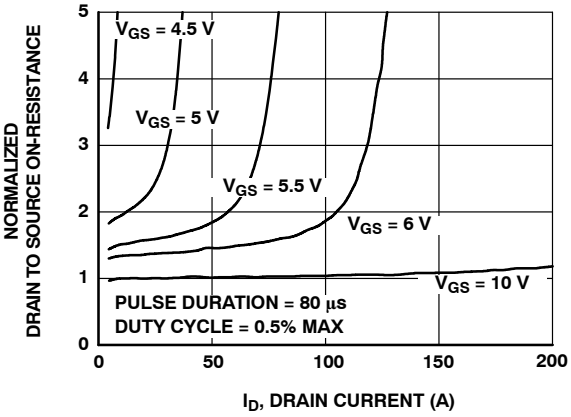

Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

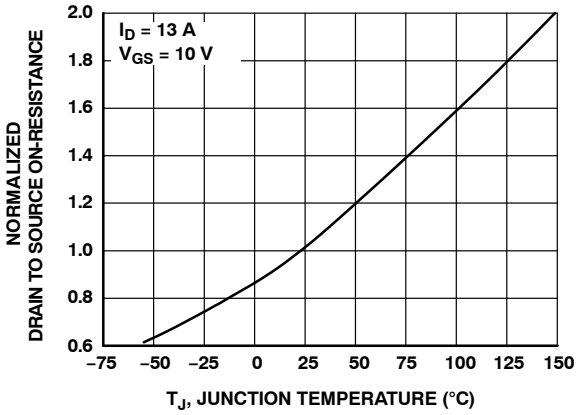

Figure 3. Normalized On Resistance vs. Junction Temperature

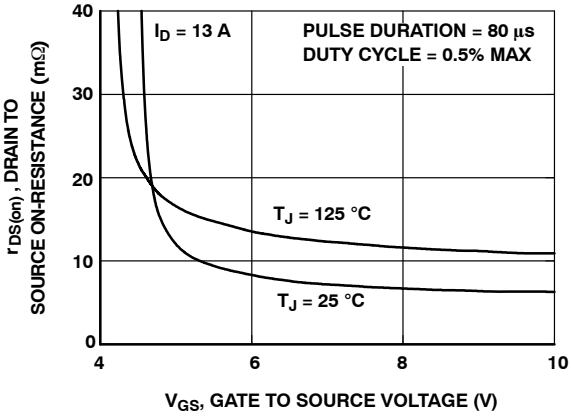

Figure 4. On-Resistance vs. Gate to Source Voltage

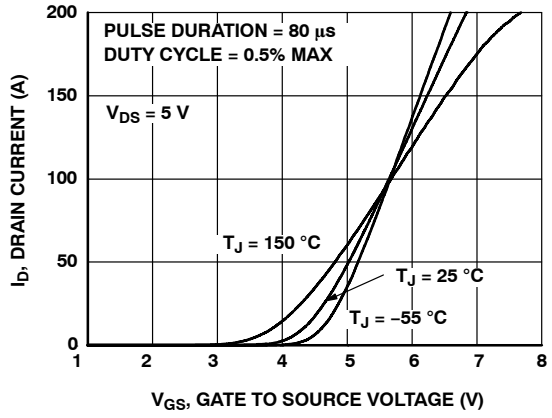

Figure 5. Transfer Characteristics

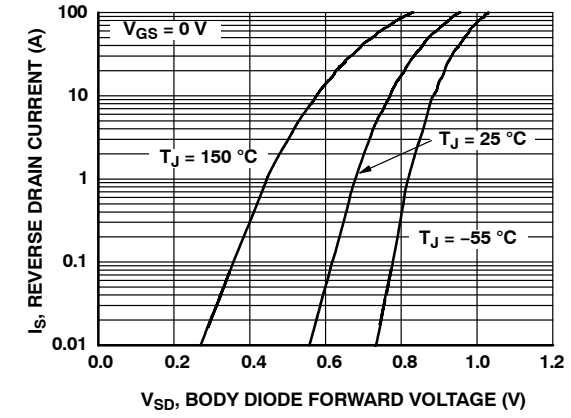

Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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TYPICAL CHARACTERISTICS (continued)

(T_J = 25 °C unless otherwise noted)

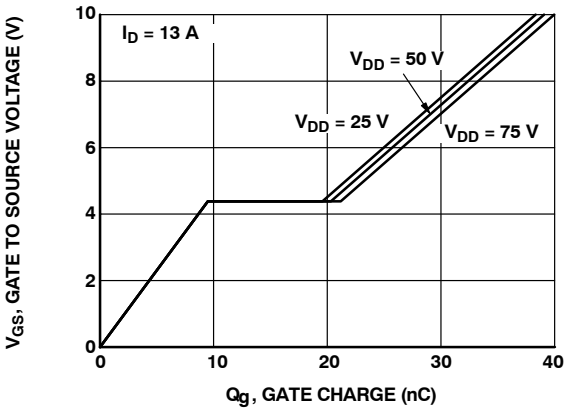

Figure 7. Gate Charge Characteristics

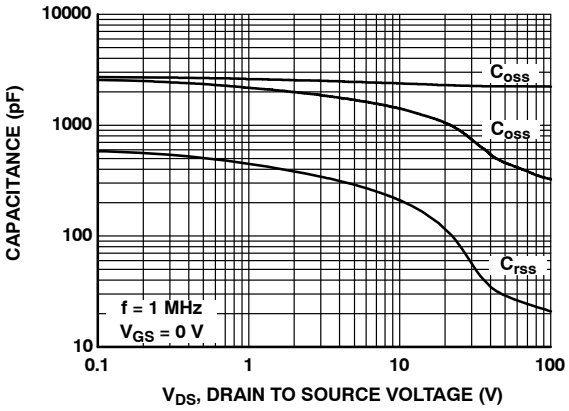

Figure 8. Capacitance vs. Drain to Source Voltage

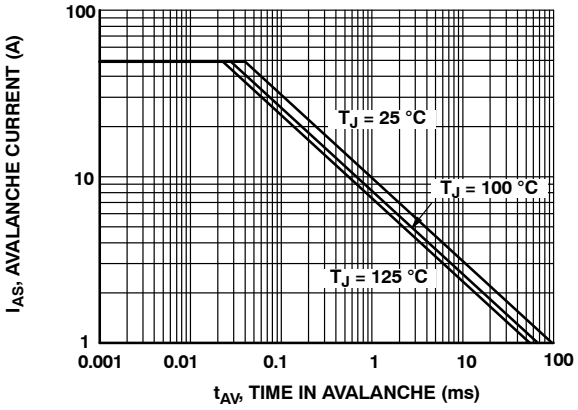

Figure 9. Unclamped Inductive Switching Capability

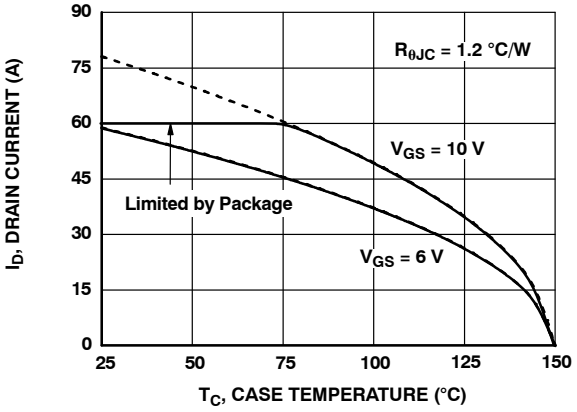

Figure 10. Maximum Continuous Drain Current vs. Case Temperature

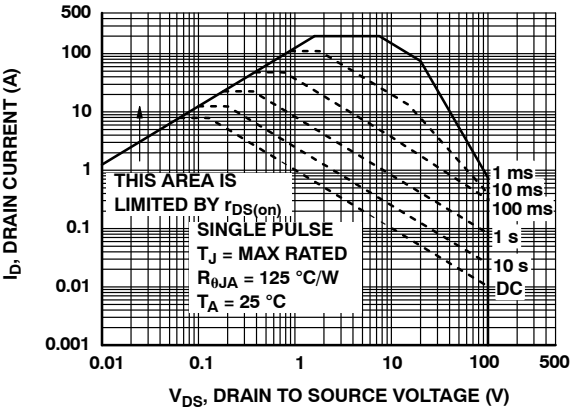

Figure 11. Forward Bias Safe Operating Area

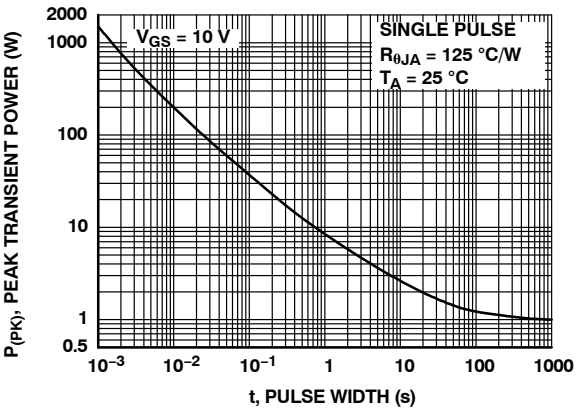

Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (continued)

(T_J = 25 °C unless otherwise noted)

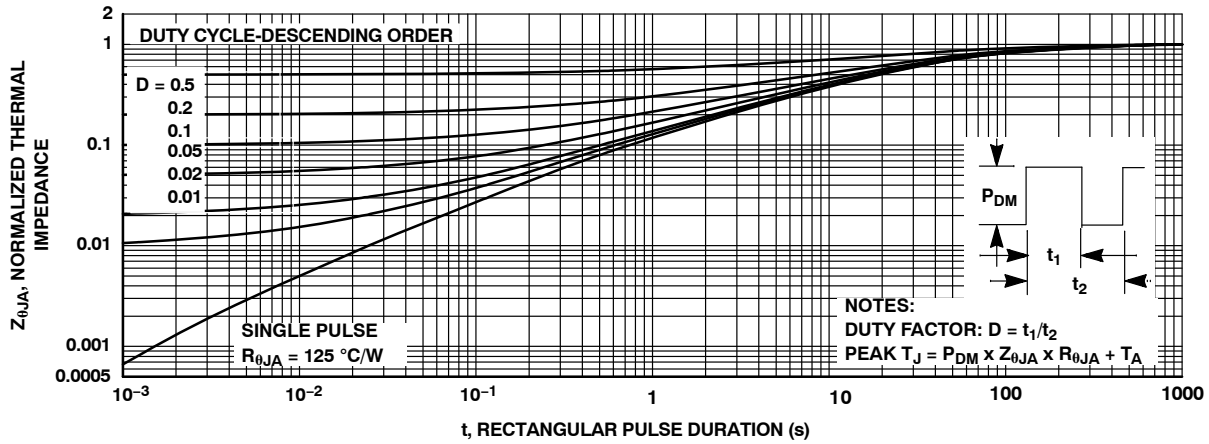

Figure 13. Junction-to-Ambient Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Shipping†
FDMS86101	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-NC	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-SN00155	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-SN00155-NC	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-SN00235	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-SN00235-NC	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-TE	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel
FDMS86101-TE-NC	FDMS86101	PQFN8 5x6, 1.27P (Pb-Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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REVISION HISTORY

Revision	Description of Changes	Date
7	Devices FDMS86101-NC, FDMS86101-SN00155-NC, FDMS86101-SN00235-NC, FDMS86101-TE-NC, FDMS86101-TE, FDMS86101-SN00155 and FDMS86101-SN00235 added and made minor formatting updates across the document.	9/4/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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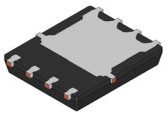
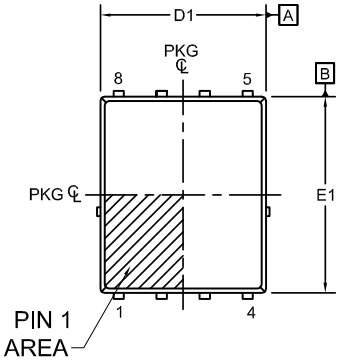
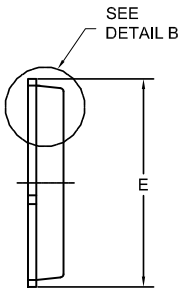


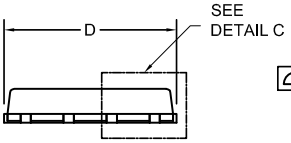
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE C

DATE 21 JAN 2022

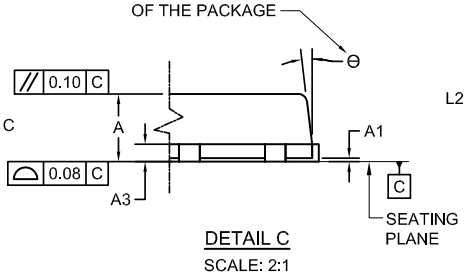


TOP VIEW

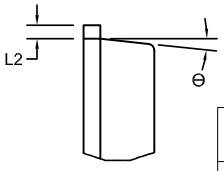




SIDE VIEW



DETAIL C
SCALE: 2:1

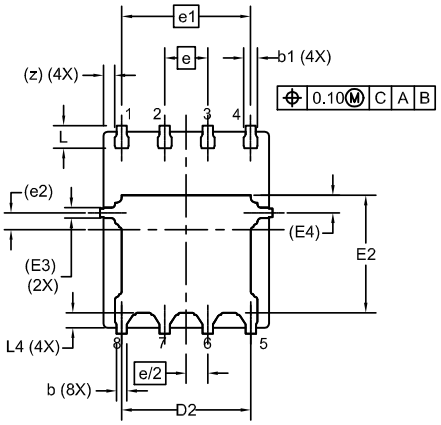


DETAIL B
SCALE: 2:1

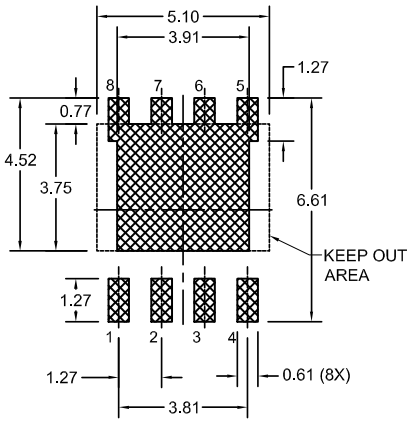
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.21	0.31	0.41
b1	0.31	0.41	0.51
A3	0.15	0.25	0.35
D	4.90	5.00	5.20
D1	4.80	4.90	5.00
D2	3.61	3.82	3.96
E	5.90	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.78
E3	0.30 REF		
E4	0.52 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
e2	0.50 REF		
L	0.51	0.66	0.76
L2	0.05	0.18	0.30
L4	0.34	0.44	0.54
z	0.34 REF		
Θ	0°	-	12°



BOTTOM VIEW



LAND PATTERN
RECOMMENDATION

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DESCRIPTION:	**PQFN8 5X6, 1.27P**		**PAGE 1 OF 1**

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onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

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Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

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